



- Staff of the RIT Epitaxy Facility are available to work with customers for any standard or customized growth or device structure.
- All growth runs are completed in-house by our staff of research scientists, all of whom have advanced training in semiconductors and epitaxy.
- Base cost for tool use shown is the per-run cost to use the tool, but does not include precursor material costs.
- For either rate, any additional time for design or product development is not included and would be a separate charge.

Source/ Material Costs

Source/ Material Costs are based on the actual cost of materials consumed. Calculations for this cost is project specific, depending on substrate and growth requirements.

Current Options:

Wafers : GaAs, InP, GaSb (test and prime wafers)

Metal Oxide: TMAI/ TEGa/ TMGa/ TTBAI/ DEZn/ TMIn/ TBAs/ TMSb

Hydrides: AsH₃ / PH₃

Base Rates for MOVPE Operation

	Federal Rates (RIT and other University customers)	Commercial Rates (all others)
Base Cost/ Run	\$100.25	\$162.25

The Base Cost/ Run is applied to all MOVPE growth and is a per run charge. Projects are invoiced monthly.

- RIT recently completed installation of a new Aixtron Close Coupled Showerhead (CCS) MOCVD
 - 3x2", 1x3" and 1x4" capability
 - **Epitaxy of III-V compounds of As, P and Sb**
 - In-situ diagnostic LayTec EpiTT-Curve system gives real time information of temperature, stress, strain and surface roughness
 - Materials used for advanced applications in solar energy, integrated photonics, nanomanufacturing, infrared detectors and next generation electronics

